PNP Epitaxial Planar Silicon Transistor NPN Triple Diffused Planar Silicon Transistor



2SB817C/2SD1047C

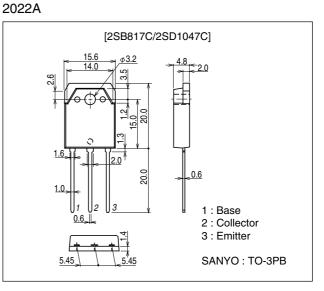
140V / 12A, AF 80W Output Applications

Features

- Large current capacitance.
- Wide ASO and high durability against breakdown.
- Adoption of MBIT process.

Package Dimensions

unit : mm



Specifications

():2SB817C

Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|--------|------------|-------------|------|
| Collector-to-Base Voltage | VCBO | | (-)160 | V |
| Collector-to-Emitter Voltage | VCEO | | (-)140 | V |
| Emitter-to-Base Voltage | VEBO | | (-)6 | V |
| Collector Current | IC | | (-)12 | А |
| Collector Current (Pulse) | ICP | | (-)20 | Α |
| Collector Dissipation | PC | | 2.5 | W |
| | | Tc=25°C | 120 | W |
| Junction Temperature | Tj | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Electrical Characteristics at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--------------------------|--------|---|---------|-----|--------|------|
| | | | min | typ | max | Onit |
| Collector Cutoff Current | ICBO | V _{CB} =(-)160V, I _E =0 | | | (-)0.1 | mA |
| Emitter Cutoff Current | IEBO | V _{EB} =(-)4V, I _C =0 | | | (-)0.1 | mA |
| DC Current Gain | hFE1 | V _{CE} =(-)5V, I _C =(-)1A | 100 | | 200 | |
| | hFE2 | V _{CE} =(-)5V, I _C =(-)5A | 35 | | | |

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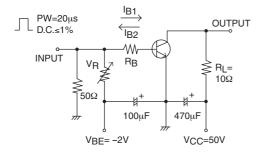
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Continued from preceding page.

| Parameter | Symbol | Conditions | | Ratings | | |
|---|-----------------------|---|--------|------------|--------|------|
| | | | min | typ | max | Unit |
| Gain-Bandwidth Product | fT | V _{CE} =(-)5V, I _C =(-)1A | | (10)15 | | MHz |
| Output Capacitance | Cob | V _{CB} =(-)10V, f=1MHz | | (280)140 | | pF |
| Base-to-Emitter Voltage | VBE | V _{CE} =(-)5A, I _C =(-)5A | | | 1.5 | V |
| Collector-to-Emitter Saturation Voltage | V _{CE} (sat) | IC=(-)5A, IB=(-)0.5A | | (- 0.3)0.2 | (-)2.0 | V |
| Collector-to-Base Breakdown Voltage | V(BR)CBO | IC=(-)5mA, IE=0 | (-)160 | | | V |
| Collector-to-Emitter Breakdown Voltage | V(BR)CEO | IC=(-)50mA, RBE=∞ | (-)140 | | | V |
| Emitter-to-Base Breakdown Voltage | V(BR)EBO | IE=(-)5mA, IC=0 | (-)6 | | | V |
| Turn-On Time | ton | See specified Test Circuit. | | (0.45)0.56 | | μs |
| Storage Time | tstg | See specified Test Circuit. | | (1.75)3.3 | | μs |
| Fall Time | tf | See specified Test Circuit. | | (0.25)0.4 | | μs |

Switching Time Test Circuit



IC=10IB1= -10IB2=5A For PNP, the polarity is reversed.

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